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- (71) **Applicant (for all designated States except US):** **COR-
ANT ADVANCED TECHNOLOGY, LLC** [US/US];
116 W. 23rd Street, Suite 500, New York, NY 10011 (US).
- (72) **Inventors:** **BAEHR-JONES, Thomas**; 332 East Camino
Real Avenue, Arcadia, CA 91006 (US). **ZHANG, Yi**; 35
River Drive South Apt. 2207, Jersey City, NJ 07310 (US).
HOCHBERG, Michael, J.; 613 East 6th Street Apt 4A,
New York, NY 10009 (US). **NOVACK, Ari**; 100 W 74th
St. Apt 1N, New York, NY 10023 (US).
- (74) **Agent:** **MILSTEIN, Joseph, B.**; Milstein Zhang & Wu
LLC, 2000 Commonwealth Avenue, Suite 400, Newton,
MA 02466-2004 (US).

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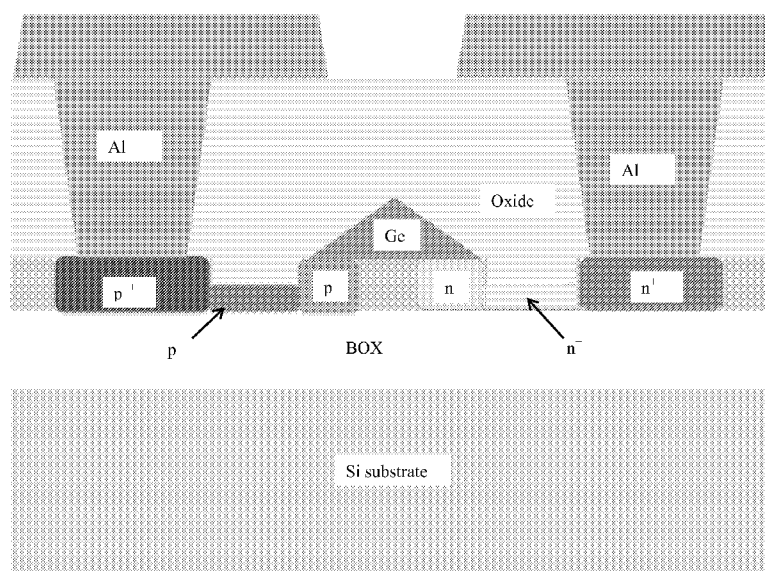
(54) **Title:** GERMANIUM METAL-CONTACT-FREE NEAR-IR PHOTODETECTOR

FIG. 2A

(57) **Abstract:** A Ge-on-Si photodetector constructed without doping or contacting Germanium by metal is described. Despite the simplified fabrication process, the device has responsivity of 1.24 A/W, corresponding to 99.2% quantum efficiency. Dark current is 40 nA at -4 V reverse bias. 3-dB bandwidth is 30 GHz.



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